SN65C3222, SN75C3222 3-V TO 5.5-V MULTICHANNEL RS-232 COMPATIBLE LINE DRIVER/RECEIVER

SLLS534B - MAY 2002 - REVISED OCTOBER 2004

- Operates With 3-V to 5.5-V V_{CC} Supply
- Operates Up To 1 Mbit/s
- Low Standby Current . . . 1 μA Typ
- External Capacitors . . . 4 × 0.1 μF
- Accepts 5-V Logic Input With 3.3-V Supply
- RS-232 Bus-Pin ESD Protection Exceeds ±15 kV Using Human-Body Model (HBM)
- Applications
 - Battery-Powered Systems, PDAs,
 Notebooks, Laptops, Palmtop PCs, and
 Hand-Held Equipment

(TOP VIEW) 20 PWRDOWN FΝΓ C1+[]2 19 🛮 V_{CC} 18 GND V+[]3 C1−∏4 17 DOUT1 16 **∏** RIN1 C2+∏5 C2- Π 6 15 **∏** ROUT1 V−**∏** 7 14 NC DOUT2 8 13 DIN1 RIN2 I 9 12 **∏** DIN2 ROUT2 ¶ 10 ∏ NC

DB, DW, OR PW PACKAGE

NC - No internal connection

description/ordering information

The SN65C3222 and SN75C3222 consist of two line drivers, two line receivers, and a dual charge-pump circuit with ± 15 -kV ESD protection pin to pin (serial-port connection pins, including GND). The devices provide the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The devices operate at data signaling rates up to 1 Mbit/s and a driver output slew rate of 24 V/ μ s to 150 V/ μ s.

The SN65C3222 and SN75C3222 can be placed in the power-down mode by setting $\overline{PWRDOWN}$ low, which draws only 1 μ A from the power supply. When the devices are powered down, the receivers remain active while the drivers are placed in the high-impedance state. Also, during power down, the onboard charge pump is disabled, V+ is lowered to V_{CC}, and V- is raised toward GND. Receiver outputs also can be placed in the high-impedance state by setting \overline{EN} high.

ORDERING INFORMATION

| TA | PACKAGE [†] | | ORDERABLE PART NUMBER | TOP-SIDE MARKING |
|---------------|----------------------|--------------|--------------------------|---------------------|
| | 0010 (D)40 | Tube of 25 | SN75C3222DW | 7500000 |
| | SOIC (DW) | Reel of 2000 | SN75C3222DWR | 75C3222 |
| −0°C to 70°C | SSOP (DB) | Reel of 2000 | SN75C3222DBR | CA3222 |
| | TCCOD (DIA) | Tube of 70 | SN75C3222PW | CA2000 |
| | TSSOP (PW) | Reel of 2000 | SN75C3222PWR | CA3222 |
| | COIC (DW) | Tube of 25 | SN65C3222DW | 0500000 |
| | SOIC (DW) | Reel of 2000 | SN65C3222DWR | 65C3222 |
| -40°C to 85°C | SSOP (DB) | Reel of 2000 | SN65C3222DBR | CB3222 |
| | TCCOD (DIA) | Tube of 70 | SN65C3222PW | CDagge |
| | TSSOP (PW) | Reel of 2000 | SN65C3222PWR | CB3222 |

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



Function Tables

EACH DRIVER

| IN | INPUTS | | | | | |
|-----|-------------|---|--|--|--|--|
| DIN | DIN PWRDOWN | | | | | |
| Х | L | Z | | | | |
| L | Н | Н | | | | |
| Н | Н | L | | | | |

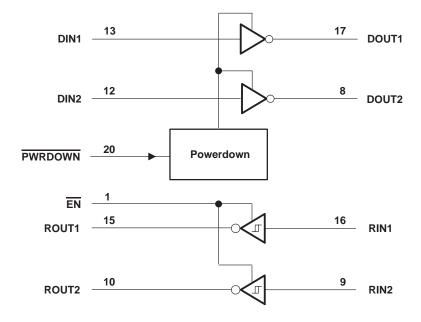
H = high level, L = low level, X = irrelevant, Z = high impedance

EACH RECEIVER

| INPU | OUTPUT | |
|------|--------|------|
| RIN | EN | ROUT |
| L | L | Н |
| Н | L | L |
| Х | Н | Z |
| Open | L | Н |

H = high level, L = low level, X = irrelevant, Z = high impedance (off), Open = input disconnected or connected driver off

logic diagram (positive logic)



SN65C3222, SN75C3222 3-V TO 5.5-V MULTICHANNEL RS-232 COMPATIBLE LINE DRIVER/RECEIVER

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

| Supply voltage range, V _{CC} (see Note 1) | 0.3 V to 6 V |
|---|----------------------------------|
| Positive output supply voltage range, V+ (see Note 1) | |
| Negative output supply voltage range, V- (see Note 1) | 0.3 V to –7 V |
| Supply voltage difference, V+ – V– (see Note 1) | 13 V |
| Input voltage range, V _I : Drivers, EN, PWRDOWN | 0.3 V to 6 V |
| Receivers | –25 V to 25 V |
| Output voltage range, VO: Drivers | |
| Receivers | 0.3 V to V _{CC} + 0.3 V |
| Package thermal impedance, θ_{JA} (see Notes 2 and 3): | DB package 70°C/W |
| | DW package 58°C/W |
| | PW package 83°C/W |
| Operating virtual junction temperature, T _J | |
| Storage temperature range, T _{stq} | –65°C to 150°C |

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to network GND.

- 2. Maximum power dissipation is a function of T_J(max), θ_{JA}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is P_D = (T_J(max) T_A)/θ_{JA}. Operating at the absolute maximum T_J of 150°C can affect reliability.
- 3. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions (see Note 4 and Figure 5)

| | | | | MIN | NOM | MAX | UNIT |
|----------------|--|-------------------------|-------------------------|-----|-----|-----|------|
| | Owner houselfer me | V _{CC} = 3.3 V | | 3 | 3.3 | 3.6 | ., |
| | Supply voltage | V _{CC} = 5 V | | 4.5 | 5 | 5.5 | V |
| ., | Deliver and control black level incort valtage | DIN EN BWBBOWN | V _{CC} = 3.3 V | 2 | | | ., |
| VIH | Driver and control high-level input voltage | DIN, EN, PWRDOWN | V _{CC} = 5 V | 2.4 | | | V |
| VIL | Driver and control low-level input voltage | DIN, EN, PWRDOWN | | | | 8.0 | V |
| ٧ _I | Driver and control input voltage | DIN, EN, PWRDOWN | | 0 | | 5.5 | V |
| ٧ _I | Receiver input voltage | | | -25 | | 25 | V |
| т. | Operating free circumperature | SN65C3222 | _ | -40 | | 85 | °C |
| TA | Operating free-air temperature | SN75C3222 | _ | 0 | | 70 | C |

NOTE 4: Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V.

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 5)

| | PARAMETER | TEST CONDITIONS | MIN | TYP‡ | MAX | UNIT |
|-----|-------------------------------------|-------------------------|-----|-------|-----|------|
| I | Input leakage current (EN, PWRDOWN) | | | ±0.01 | ±1 | μΑ |
| | Supply current | No load, PWRDOWN at VCC | | 0.3 | 1 | mA |
| Icc | Supply current (powered off) | No load, PWRDOWN at GND | | 1 | 10 | μΑ |

[‡] All typical values are at $V_{CC} = 3.3 \text{ V}$ or $V_{CC} = 5 \text{ V}$, and $T_A = 25^{\circ}\text{C}$.

NOTE 4: Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V.



DRIVER SECTION

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 5)

| | PARAMETER | TEST | CONDITIONS | MIN | TYP† | MAX | UNIT |
|----------------|--|--|---|-----|-------|-----|------|
| Vон | High-level output voltage | DOUT at $R_L = 3 \text{ k}\Omega$ to GND, | DIN = GND | 5 | 5.4 | | V |
| VOL | Low-level output voltage | DOUT at R _L = $3 \text{ k}\Omega$ to GND, | DIN = V _{CC} | -5 | -5.4 | | V |
| lн | High-level input current | VI = VCC | | | ±0.01 | ±1 | μΑ |
| IլL | Low-level input current | V _I at GND | | | ±0.01 | ±1 | μΑ |
| | Object of the first standard accommend | V _{CC} = 3.6 V, | VO = 0 V | | ±35 | ±60 | A |
| los | Short-circuit output current‡ | V _{CC} = 5.5 V, | VO = 0 V | | ±35 | ±90 | mA |
| r _O | Output resistance | V_{CC} , V+, and V- = 0 V, | $V_O = \pm 2 V$ | 300 | 10M | | Ω |
| 1 | Output lookage ourrent | PWRDOWN = GND | $V_O = \pm 12 \text{ V}, V_{CC} = 3 \text{ V to } 3.6 \text{ V}$ | | | ±25 | |
| loff | Output leakage current | PWRDOWN = GND | $V_O = \pm 10 \text{ V}, V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$ | | | ±25 | μΑ |

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$ or $V_{CC} = 5 \text{ V}$, and $T_A = 25^{\circ}\text{C}$.

NOTE 4: Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 4)

| | PARAMETER | - | TEST CONDITIONS | MIN | TYP† | MAX | UNIT |
|----------------------------------|---|---|--|------|------|-----|--------|
| | | | C _L = 1000 pF | 250 | | | |
| Maximum data rate (see Figure 1) | | $R_L = 3 k\Omega$, One DOUT switching | $C_L = 250 \text{ pF}, \qquad V_{CC} = 3 \text{ V to } 4.5 \text{ V}$ | 1000 | | | kbit/s |
| | | ono Boot ownorming | $C_L = 1000 \text{ pF}, \qquad V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$ | 1000 | | | |
| t _{sk(p)} | Pulse skew§ | C _L = 150 pF to 2500 pF | $R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega,$ See Figure 2 | | 300 | | ns |
| SR(tr) | Slew rate, transition region (see Figure 1) | R _L = 3 kΩ to 7 kΩ, V _{CC} = 3.3 V | C _L = 150 pF to 1000 pF | 18 | | 150 | V/μs |

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$ or $V_{CC} = 5 \text{ V}$, and $T_A = 25^{\circ}\text{C}$.

\$ Pulse skew is defined as $|tp_{LH} - tp_{HL}|$ of each channel of the same device. NOTE 4: Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V.



[‡] Short-circuit durations should be controlled to prevent exceeding the device absolute power-dissipation ratings, and not more than one output should be shorted at a time.

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RECEIVER SECTION

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 5)

| | PARAMETER | TEST CONDITIONS | MIN | TYP† | MAX | UNIT |
|------------------|---|--------------------------------|-------------------------|-------------------------|-----|------|
| Vон | High-level output voltage | $I_{OH} = -1 \text{ mA}$ | V _{CC} – 0.6 V | V _{CC} – 0.1 V | | V |
| VOL | Low-level output voltage | I _{OL} = 1.6 mA | | | 0.4 | V |
| V | Decision makes insure the seek and contrary | V _{CC} = 3.3 V | | 1.5 | 2.4 | V |
| V _{IT+} | Positive-going input threshold voltage | $V_{CC} = 5 V$ | | 1.8 | 2.4 | V |
| \/ | Nametica mains in most through and contains | V _{CC} = 3.3 V | 0.6 | 1.2 | | V |
| VIT- | Negative-going input threshold voltage | V _{CC} = 5 V | 0.8 | 1.5 | | V |
| V _{hys} | Input hysteresis (V _{IT+} - V _{IT-}) | | | 0.3 | | V |
| loff | Output leakage current | EN = V _{CC} | | ±0.05 | ±10 | μΑ |
| rį | Input resistance | V _I = ±3 V to ±25 V | 3 | 5 | 7 | kΩ |

† All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C. NOTE 4: Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4)

| | PARAMETER | TEST CONDITIONS | MIN TYPT MAX | UNIT |
|--------------------|---|---|--------------|------|
| tPLH | Propagation delay time, low- to high-level output | $C_{L} = 150$ pF, See Figure 3 | 300 | ns |
| tPHL | Propagation delay time, high- to low-level output | C _L = 150 pF, See Figure 3 | 300 | ns |
| t _{en} | Output enable time | C_L = 150 pF, R_L = 3 kΩ, See Figure 4 | 200 | ns |
| t _{dis} | Output disable time | C_L = 150 pF, R_L = 3 kΩ, See Figure 4 | 200 | ns |
| t _{sk(p)} | Pulse skew [‡] | See Figure 3 | 300 | ns |

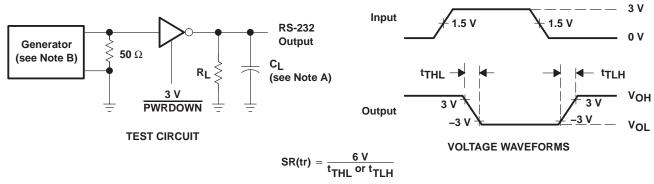
[†] All typical values are at $V_{CC} = 3.3 \text{ V}$ or $V_{CC} = 5 \text{ V}$, and $T_A = 25^{\circ}\text{C}$.

NOTE 4: Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V.



[‡] Pulse skew is defined as |tpLH - tpHL| of each channel of the same device.

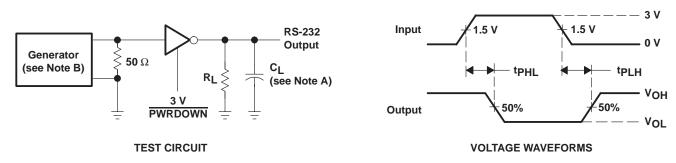
PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_O = 50~\Omega$, 50% duty cycle, $t_\Gamma \le 10$ ns. $t_f \le 10$ ns.

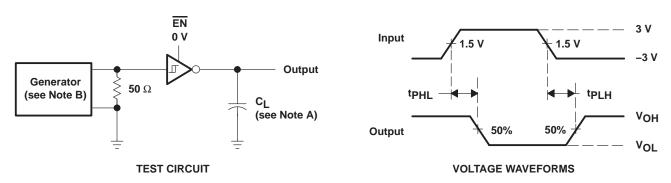
Figure 1. Driver Slew Rate



NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_O = 50 \Omega$, 50% duty cycle, $t_f \le 10$ ns. $t_f \le 10$ ns.

Figure 2. Driver Pulse Skew



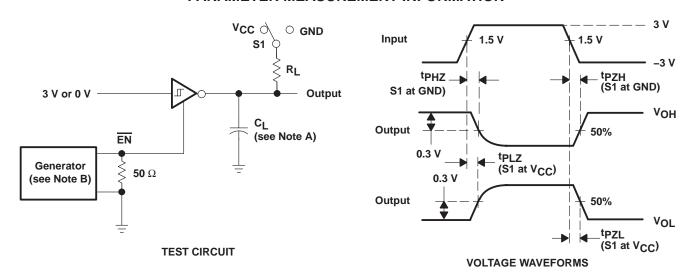
NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: $Z_O = 50 \Omega$, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

Figure 3. Receiver Propagation-Delay Times



PARAMETER MEASUREMENT INFORMATION

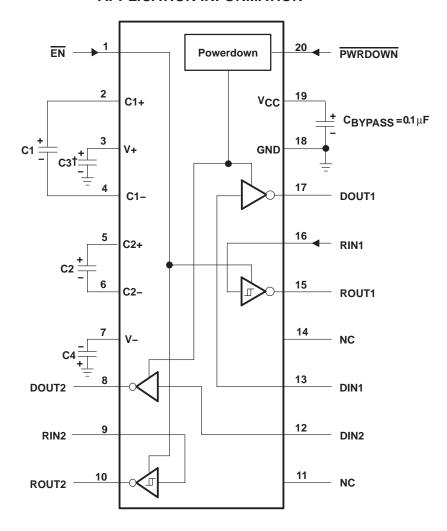


NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: $Z_O = 50 \ \Omega$, 50% duty cycle, $t_\Gamma \le 10 \ ns$, $t_f \le 10 \ ns$.

Figure 4. Receiver Enable and Disable Times

APPLICATION INFORMATION



 $^\dagger\text{C3}$ can be connected to VCC or GND.

NOTES: A. Resistor values shown are nominal.

B. NC - No internal connection

V_{CC} vs CAPACITOR VALUES

| vcc | C1 | C2, C3, and C4 | | |
|-------------------|-------------------------|------------------------|--|--|
| 3.3 V \pm 0.3 V | 0.1 μ F | 0.1 μ F | | |
| 5 V ± 0.5 V | 0.047 μ F | 0.33 μF | | |
| 3 V to 5.5 V | 0.1 μ F | 0.47 μ F | | |

Figure 5. Typical Operating Circuit and Capacitor Values



20-Aug-2011

PACKAGING INFORMATION

| Orderable Device | Status (1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan ⁽²⁾ | Lead/ Ball Finish | MSL Peak Temp ⁽³⁾ | Samples (Requires Login) |
|------------------|------------|--------------|--------------------|------|-------------|----------------------------|----------------------|------------------------------|-----------------------------|
| SN65C3222DBR | ACTIVE | SSOP | DB | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN65C3222DBRE4 | ACTIVE | SSOP | DB | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN65C3222DBRG4 | ACTIVE | SSOP | DB | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN65C3222DWR | ACTIVE | SOIC | DW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN65C3222DWRE4 | ACTIVE | SOIC | DW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN65C3222DWRG4 | ACTIVE | SOIC | DW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN65C3222PW | ACTIVE | TSSOP | PW | 20 | 70 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN65C3222PWE4 | ACTIVE | TSSOP | PW | 20 | 70 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN65C3222PWG4 | ACTIVE | TSSOP | PW | 20 | 70 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN65C3222PWR | ACTIVE | TSSOP | PW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN65C3222PWRE4 | ACTIVE | TSSOP | PW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN65C3222PWRG4 | ACTIVE | TSSOP | PW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN75C3222DBR | ACTIVE | SSOP | DB | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN75C3222DBRE4 | ACTIVE | SSOP | DB | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN75C3222DBRG4 | ACTIVE | SSOP | DB | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN75C3222DW | ACTIVE | SOIC | DW | 20 | 25 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN75C3222DWE4 | ACTIVE | SOIC | DW | 20 | 25 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |





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| Orderable Device | Status ⁽¹⁾ | Package Type | Package Drawing | Pins | Package Qty | Eco Plan ⁽²⁾ | Lead/ Ball Finish | MSL Peak Temp ⁽³⁾ | Samples (Requires Login) |
|------------------|-----------------------|--------------|--------------------|------|-------------|----------------------------|----------------------|------------------------------|-----------------------------|
| SN75C3222DWG4 | ACTIVE | SOIC | DW | 20 | 25 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN75C3222DWR | ACTIVE | SOIC | DW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN75C3222DWRE4 | ACTIVE | SOIC | DW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN75C3222DWRG4 | ACTIVE | SOIC | DW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN75C3222PW | ACTIVE | TSSOP | PW | 20 | 70 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN75C3222PWE4 | ACTIVE | TSSOP | PW | 20 | 70 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN75C3222PWG4 | ACTIVE | TSSOP | PW | 20 | 70 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN75C3222PWR | ACTIVE | TSSOP | PW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN75C3222PWRE4 | ACTIVE | TSSOP | PW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| SN75C3222PWRG4 | ACTIVE | TSSOP | PW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.



PACKAGE OPTION ADDENDUM

20-Aug-2011

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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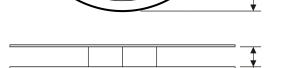
PACKAGE MATERIALS INFORMATION

14-Jul-2012 www.ti.com

TAPE AND REEL INFORMATION

REEL DIMENSIONS





TAPE DIMENSIONS



| A0 | Dimension designed to accommodate the component width |
|----|---|
| В0 | Dimension designed to accommodate the component length |
| K0 | Dimension designed to accommodate the component thickness |
| W | Overall width of the carrier tape |
| P1 | Pitch between successive cavity centers |

TAPE AND REEL INFORMATION

*All dimensions are nominal

| Device | Package Type | Package Drawing | | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|--------------|-----------------|--------------------|----|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| SN65C3222DBR | SSOP | DB | 20 | 2000 | 330.0 | 16.4 | 8.2 | 7.5 | 2.5 | 12.0 | 16.0 | Q1 |
| SN65C3222DWR | SOIC | DW | 20 | 2000 | 330.0 | 24.4 | 10.8 | 13.0 | 2.7 | 12.0 | 24.0 | Q1 |
| SN65C3222PWR | TSSOP | PW | 20 | 2000 | 330.0 | 16.4 | 6.95 | 7.1 | 1.6 | 8.0 | 16.0 | Q1 |
| SN75C3222DBR | SSOP | DB | 20 | 2000 | 330.0 | 16.4 | 8.2 | 7.5 | 2.5 | 12.0 | 16.0 | Q1 |
| SN75C3222DWR | SOIC | DW | 20 | 2000 | 330.0 | 24.4 | 10.8 | 13.0 | 2.7 | 12.0 | 24.0 | Q1 |
| SN75C3222PWR | TSSOP | PW | 20 | 2000 | 330.0 | 16.4 | 6.95 | 7.1 | 1.6 | 8.0 | 16.0 | Q1 |

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*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|--------------|--------------|-----------------|------|------|-------------|------------|-------------|
| SN65C3222DBR | SSOP | DB | 20 | 2000 | 367.0 | 367.0 | 38.0 |
| SN65C3222DWR | SOIC | DW | 20 | 2000 | 367.0 | 367.0 | 45.0 |
| SN65C3222PWR | TSSOP | PW | 20 | 2000 | 367.0 | 367.0 | 38.0 |
| SN75C3222DBR | SSOP | DB | 20 | 2000 | 367.0 | 367.0 | 38.0 |
| SN75C3222DWR | SOIC | DW | 20 | 2000 | 367.0 | 367.0 | 45.0 |
| SN75C3222PWR | TSSOP | PW | 20 | 2000 | 367.0 | 367.0 | 38.0 |

DW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AC.



DW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Refer to IPC7351 for alternate board design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC—7525
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



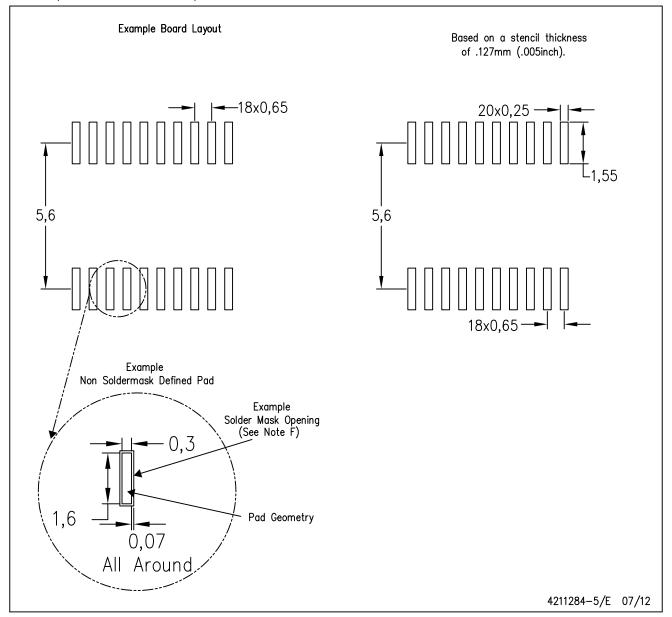
NOTES:

- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



DB (R-PDSO-G**)

PLASTIC SMALL-OUTLINE

28 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-150

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